3DD162(3DD163)

NPN Silicon Low Frequency High Power Transistor

Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications						Test Condition
			A	B	C	D	E	F	
Collector-Emitter Voltage	V_{CEO}	V	50	100	150	200	250	300	
Emitter-Base Voltage	V_{EBO}	V	5						
Max. Collector Current	I_{CM}	A	7.5						
Max. Collector Dissipation	P_{CM}	W	75						T_C:75°C
Junction Temperature	T_{jm}	°C	175						
Storage Temperature	T_{stg}	°C	-55~+175						
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:1.0						A:V_{CE}=30V;B:V_{CE}=50V; C~F:V_{CE}=100V
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:1.2						I_C=3.75A,I_B=0.38A
DC Current Gain	h_{FE}		Min.:15,Max.:180						V_{CE}=5V,I_C=3.75A
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	A	B	C	D	E	F	I_C=3mA
			50	100	150	200	250	300	
C-Base Breakdown Voltage	$V_{(BR)CBO}$	V	80	150	200	250	350	400	I_C=3mA
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5						I_E=2mA

h_{FE} Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	15~25	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions: